

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.(original) A liftoff method for photolithography, comprising:

depositing a layer of photoresist on a substrate;

exposing and developing said photoresist layer thereby forming a photoresist pattern having sidewalls and an upper surface;

irradiating said upper surface with an ion beam having a direction parallel to said sidewalls, said ion beam comprising ions whose energy is too low to sputter said layer of photoresist;

maintaining said ion beam irradiation for a time period whereby a hardened layer is formed that extends a distance downwards from said upper surface, all remaining photoresist being unhardened;

then exposing said photoresist pattern to ozone whereby said sidewalls are eroded and said hardened layer is unchanged so that the hardened layer overhangs the unhardened layer;

depositing a layer of a material onto all horizontal surfaces to a thickness that is less than that of said unhardened photoresist layer; and

selectively removing said unhardened photoresist layer whereby all of said material that is deposited onto said hardened photoresist layer is lifted off.

2. (original) The liftoff method recited in claim 1 wherein said layer of photoresist is a negative resist or a positive resist.

3. (original) The liftoff method recited in claim 1 wherein said layer of photoresist is deposited to a thickness between about 0.1 and 0.4 microns.

4. (original) The liftoff method recited in claim 1 wherein said ion beam has an energy between about 50 and 200 volts.

5. (original) The liftoff method recited in claim 1 wherein said time period for which said ion beam irradiation is maintained is between about 2 and 20 minutes.

6. (original) The liftoff method recited in claim 1 wherein said distance for which said hardened layer extends downwards is between about 100 and 500 Angstroms.

7. (currently amended) The liftoff method recited in claim 1 wherein the step of exposing said photoresist pattern to ozone further comprises placing the wafers in an ozone chamber, heating them to between 70 and 150 [[%]] °C at an ozone concentration of between 10 to 200 gm/m³ at an ozone flow rate of 1 to 100 L/minute for between 1 and 60 minutes.

8. (original) The liftoff method recited in claim 1 wherein said hardened layer overhangs the unhardened layer by between about 0.01 and 0.1 microns on each side.

9. (currently amended) The liftoff method recited in claim 1 wherein the step of selectively removing said unhardened photoresist layer further comprises using N-methyl-2-pyrrolidone at a temperature between 50 and 90 [[%]] °C for 30 to 60 minutes.

10 – 31. Canceled.

32. (currently amended) A photoresist pattern suitable for liftoff, comprising;
a single photoresist layer;
said single photoresist layer further consisting of an upper portion that is resistant to chemical attack and a lower portion that is susceptible to chemical attack; and
said upper portion overhanging said lower portion by between about 0.01 and 0.1 microns on each side.

33. (original) The photoresist pattern described in claim 32 wherein said single layer of photoresist has a thickness between about 0.1 and 0.4 microns

34. (original) The photoresist pattern described in claim 32 wherein said upper portion of photoresist has a thickness between about 100 and 500 Angstroms.

35. (canceled)